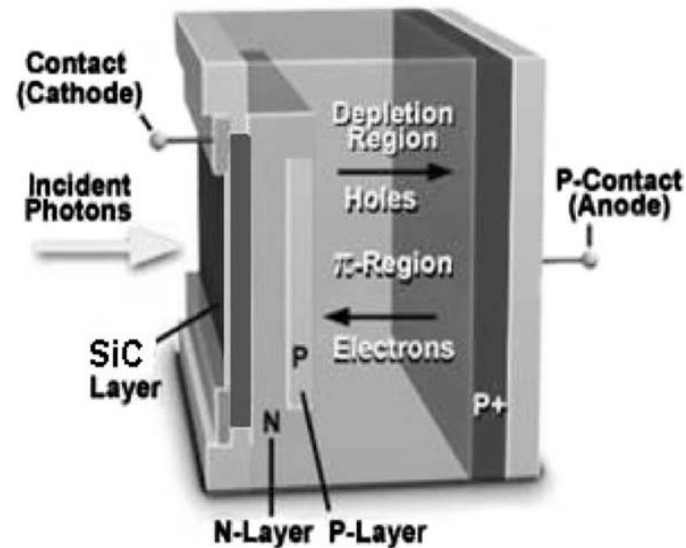

12Gev Upgrade. Silicon Photo Multipliers for Hall-B (CTOF) and Hall-D applications.

F.Barbosa, V.Baturin, A.Somov,
Jlab
I.Tolstukhin
MEPhI

Jul-2011

PRINCIPLE OF OPERATION

- 1) thin p-type layer
- 2) thick lightly doped p-layer
- 3) heavily doped p+ layer.



V. Golovin, V. Saveliev

Novel type of avalanche photo detector with Geiger mode operation

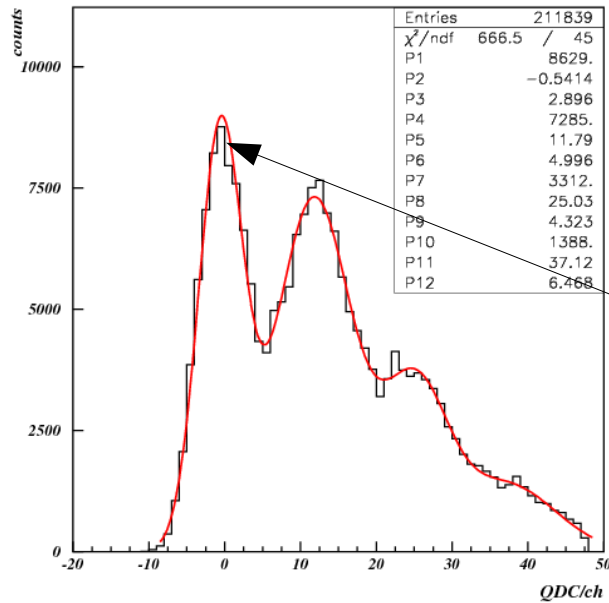
Center of Perspective Technology and Apparatus, Moscow, Russia
Obninsk State University of Nuclear Engineering, Obninsk, Russia

Nuclear Instruments and Methods in Physics Research A 518 (2004) 560-564

SiPM-3 Photon Counting with 470 nm-LED

No LED light

Hz.

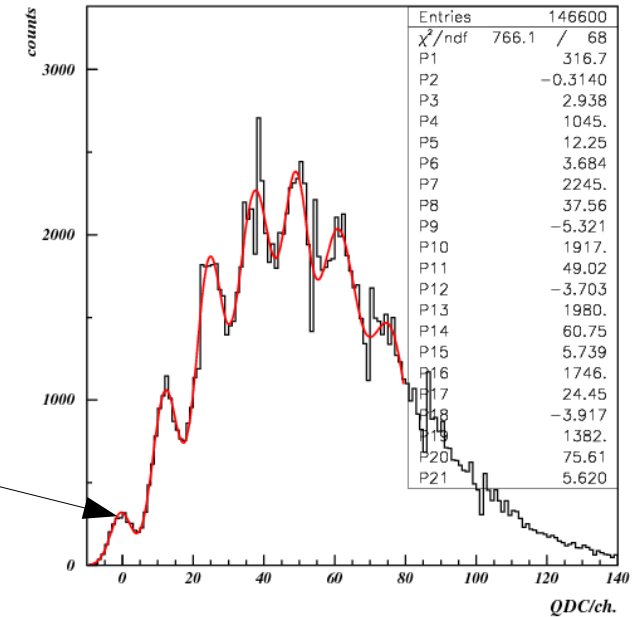


QDC counts

pedestal

~4 pixel fired by LED

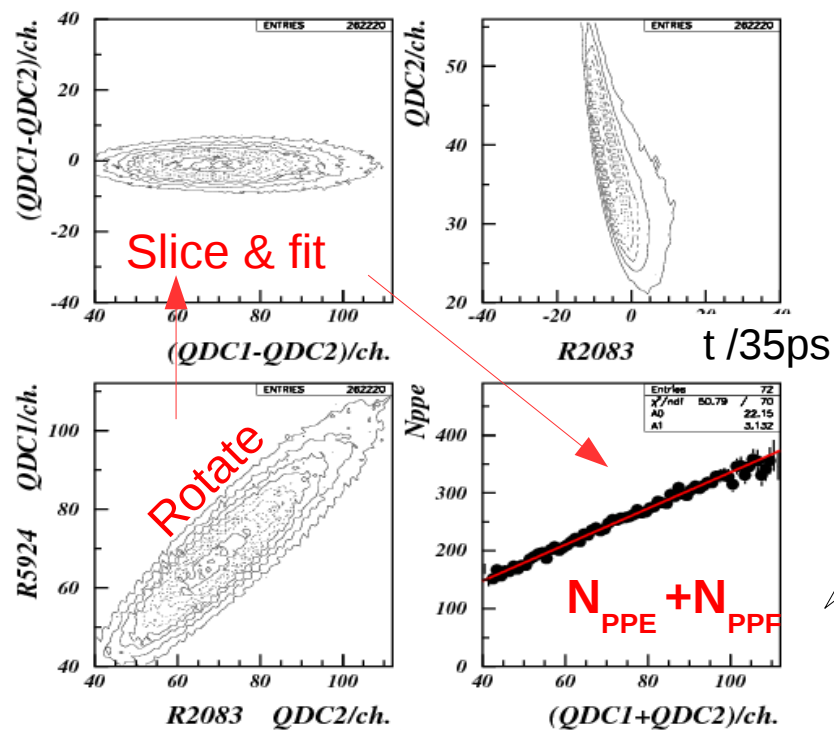
Hz.



PMT at the opposite side of Bench Setup has been calibrated.

Time resolution makes no sense without referencing N_{ppe} and N_{ppf}

We determine $N_e = N_{PPE} + N_{PPF}$ from QDC spectra of two PMs.

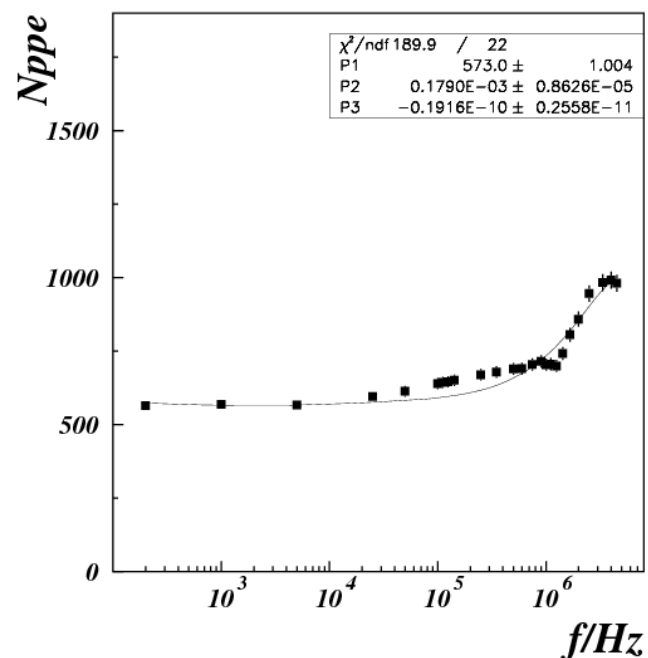
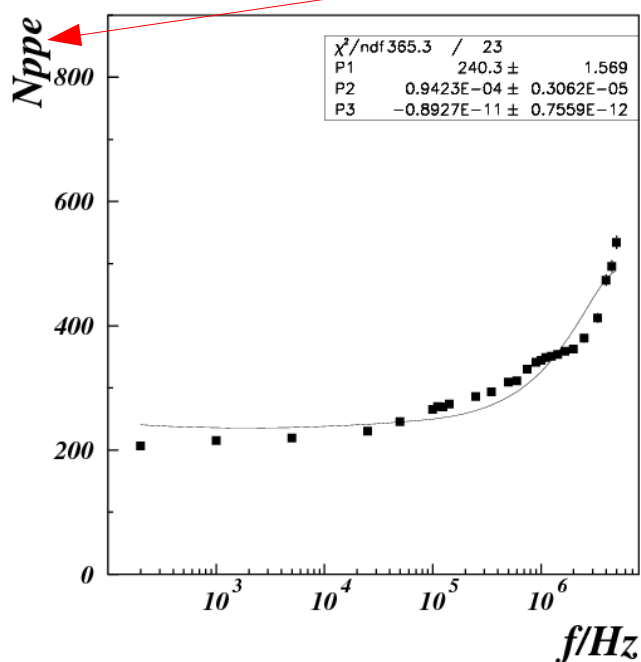


$$N_e = (N_{ppe} + N_{ppf}) = \frac{(Q_1 + Q_2)^2}{\text{var}(Q_1 - Q_2)}$$

- We determine $N_e = N_{ppe} + N_{ppf}$ that changes linearly with QDC readout.
- N_{ppe} in the reference PMT may be determined independently .

Number of photo electrons. Measuring method-2

$$\sigma_{R2083} = \sqrt{\frac{\tau_p^2}{N_{ppe}}}, \quad \text{where} \quad \tau_p = 2.9 \text{ ns}$$



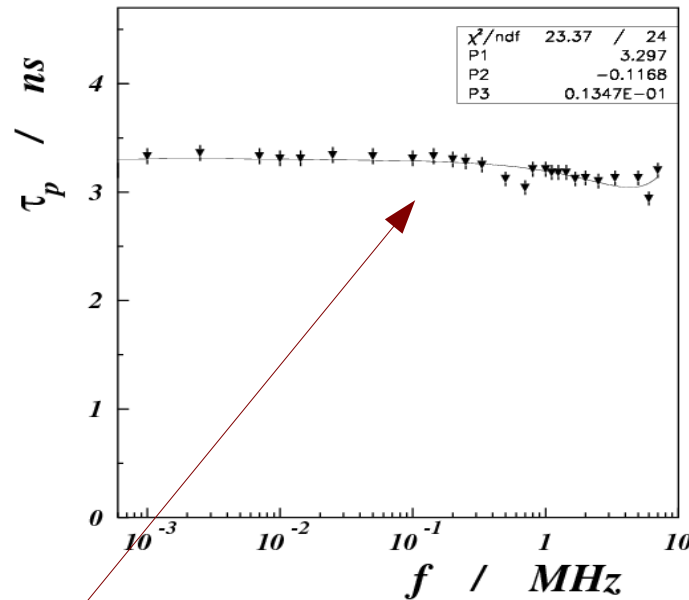
$$N_{ppf} + N_{ppe} = (Q_1 + Q_2)^2 / \text{var}(Q_1 - Q_2)$$

$$N_{ppe} = \tau_p^2 / \sigma_{R2083} = 0.17 N_\gamma$$

- Time resolutions of R2083 follows Stat. Law with linearly increasing N_γ
- We determine Quantum efficiency of the SiPM at low rate/flux.

Time resolution of reference PMT.

$$\sigma_{R2083} = \sqrt{\frac{\tau_p^2}{0.5N_e}} \quad \text{vs.} \quad \sigma_{R2083} = \sqrt{\frac{\tau_p^2}{N_{ppe}}}; \tau_p - \text{signal rise time}$$



$$N_e = (Q_p + Q_s) N_\gamma$$

$$\sqrt{\frac{1}{2} \left(1 + \frac{Q_s}{Q_p}\right)} = \frac{\tau_p}{2.9}$$

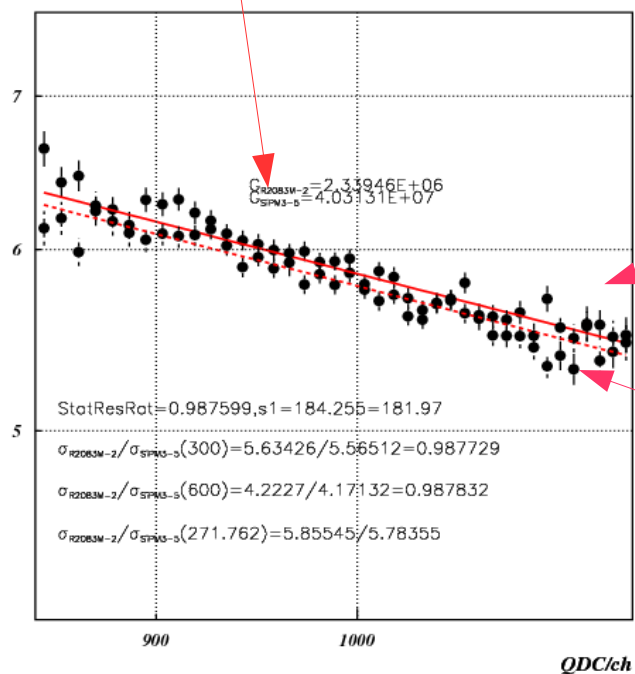
- Fit parameter $\tau_p = \mathbf{3.3 \text{ ns}}$. Stable within $\pm 5\%$ up to 7 MHz.
- The rise signal time is $\mathbf{2.9 \text{ ns}}$. The difference is due to $Q_s > Q_p = 0.17$ at 475 nm.
- **Re-normalizing** to N_{ppe} we determine $Q_s = \mathbf{0.27 \pm 0.07}$

Example. R2083 vs. SiPM3. Time Resolution at Bias Voltage 68.83 V

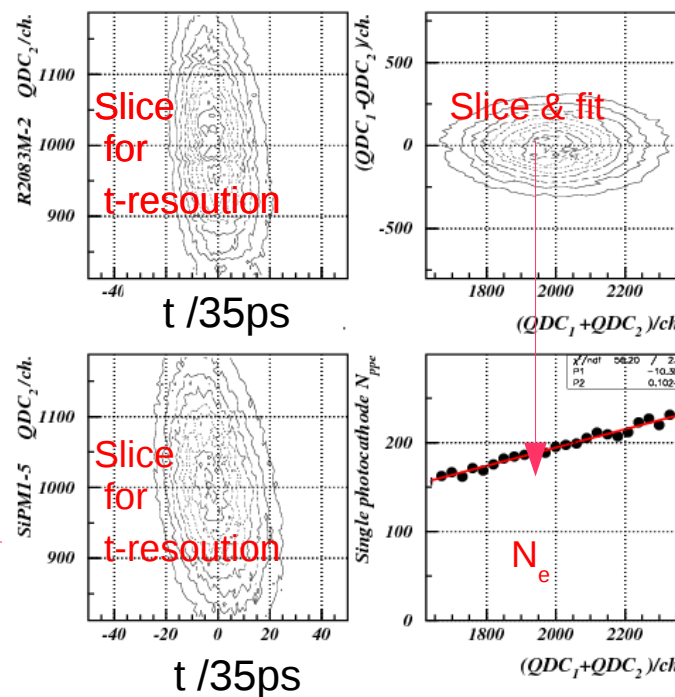
Fit function:
$$\sigma_{PM} = \sqrt{\frac{\sigma_s^2}{N_e/2} + \sigma_e^2}, \quad \sigma_e = 21 \text{ ps}$$

$\sigma/35\text{ps}$

R2083M-2(-2800V),vs.SiPM3-5(+68.83 V),470nm-LED. Run0910 at 2500 Hz.



R2083M-2(-3000 V),vs.SiPM1-5(+70.20 V),470nm-LED. Run0752 at 100000 Hz.

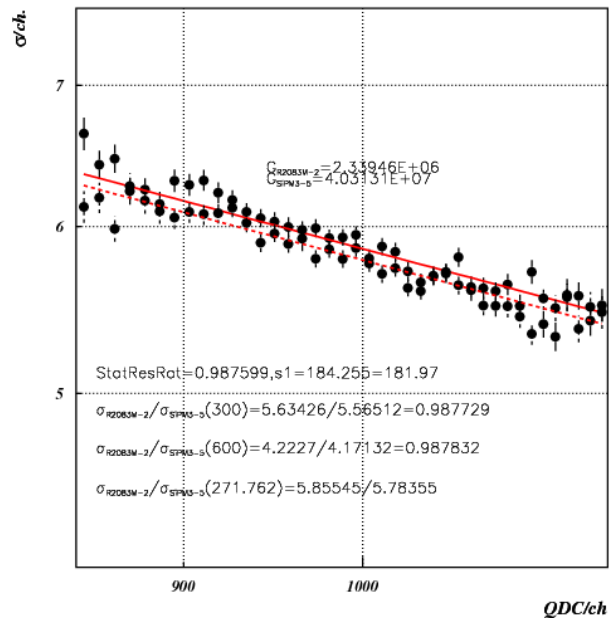


- Time resolutions of both R2083 and SiPM3 **follows the Statistical Law.**
- We determine constant σ_s from each measurement.

Comparative measurements (σ_{R2083} vs. σ_{SiPM3})

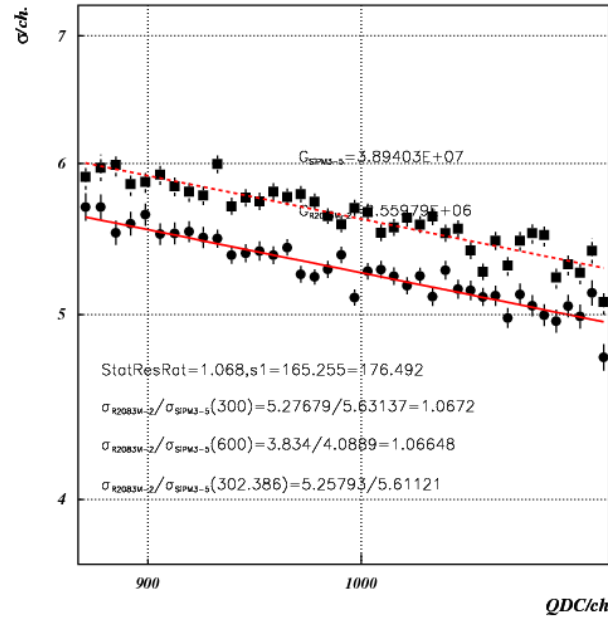
2.5 KHz

R2083M-2(-2800V).vs.SiPM3-5(+68.83 V).470nm-LED. Run0910 at 2500 Hz.



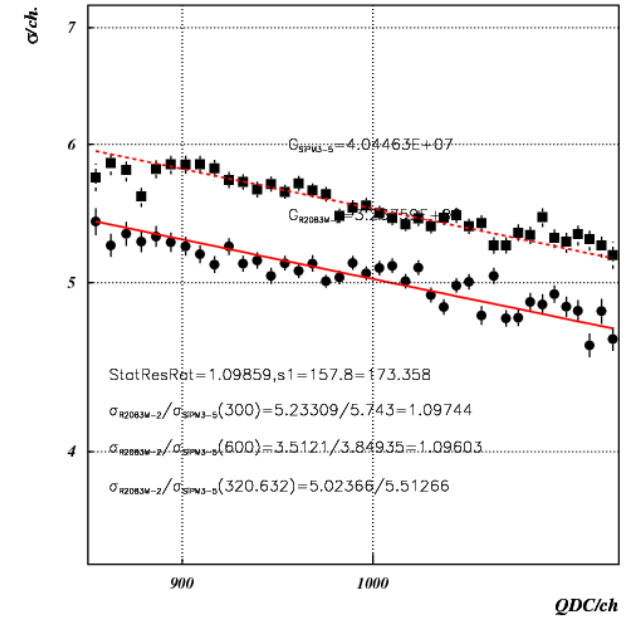
1.43 MHz

R2083M-2(-2800V).vs.SiPM3-5(+68.83 V).470nm-LED. Run0928 at 1430000 Hz.



3.3 MHz

R2083M-2(-2800V).vs.SiPM3-5(+68.83 V).470nm-LED. Run0932 at 3330000 Hz.



- SiPM resolution is a function of τ , f , and N_Y
- Reasonable parameterization is required

Parameterization (σ_{R2083} vs. σ_{SiPM3})

$$\sigma_{R2083} = \frac{\tau_p}{\sqrt{Q_p N_\gamma}}$$

$$\sigma_{SiPM} = \frac{\tau_s}{\sqrt{Q_s(f, N_\gamma) N_\gamma}}$$

$$\sigma_{SiPM3} = \alpha \sigma_{R2083} \left(\frac{N_{ppe}}{N_{pix}} \right)^{\frac{1}{2}} \left(1 - \exp\left(-\frac{Q_s N_\gamma}{N_{pix}}\right) \right)^{\frac{-1}{2}} \left(1 - \frac{Q_s N_\gamma}{N_{pix}} \right)^{\frac{-t_p f}{2}}$$

τ_p - measured PMT signal rise time

N_γ - measured number of photons

Q_s - quantum efficiency of SiPM at $f \rightarrow 0$ and $N_\gamma \rightarrow 0$

$Q_p = 0.17$; Q_s may be estimated

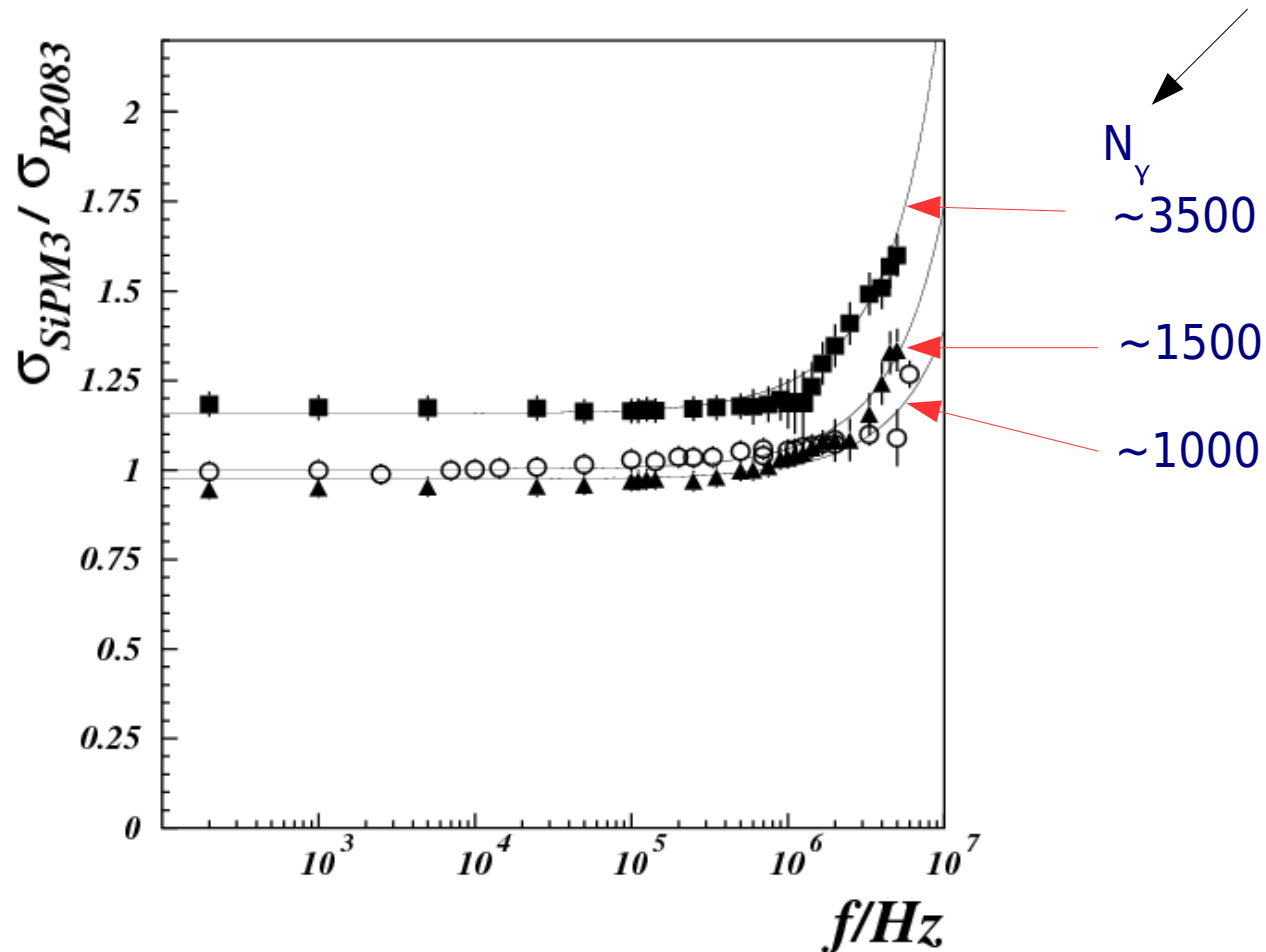
N_{pix} - nominal number of pixels

t_p - unknown pixel dead time

- Our goal is to determine experimentally α , Q_s , and t_p

Comparative measurements of σ_{R2083} vs. σ_{SiPM3}

$$\sigma_{SiPM3} = (1 \pm 0.05) \sigma_{R2083} \left(\frac{Q_s N_y}{N_{pix}} \right)^{\frac{1}{2}} \left(1 - \exp\left(-\frac{Q_s N_y}{N_{pix}}\right) \right)^{-\frac{1}{2}} \left(1 - \frac{Q_s N_y}{N_{pix}} \right)^{-\frac{t_p f}{2}}$$

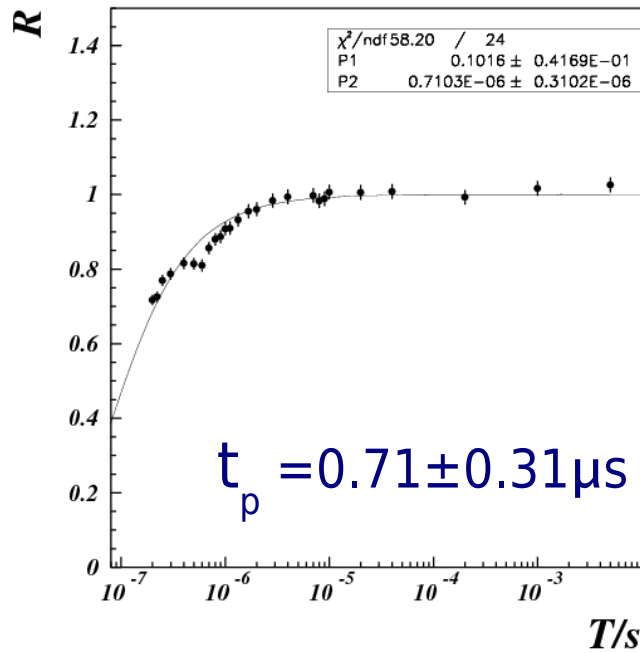


- Time resolutions of SiPM3 follows the selected parameterization with
 - $t_p = 0.8 \pm 0.3 \mu s$
 - $Q_s = 0.3 \pm 0.05$ provided $Q_p = 0.17$ at 475 nm

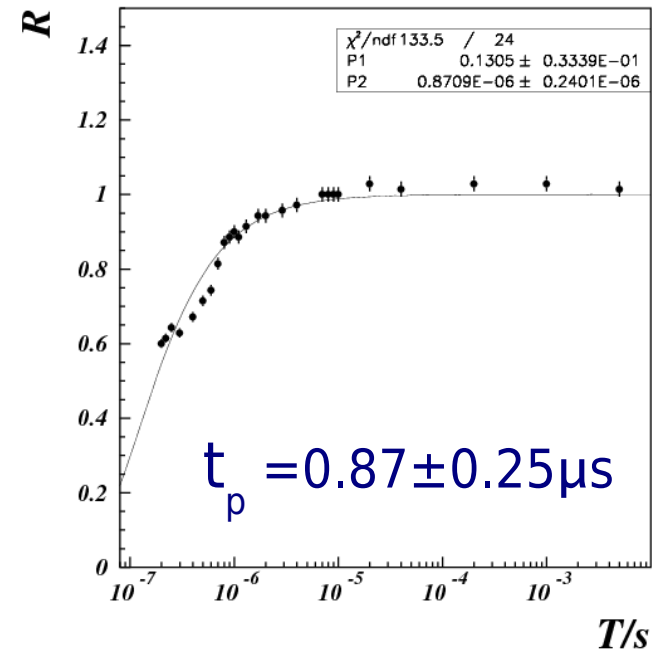
SiPM response function R and SiPM dead time t_p

$$R = \left(1 - \frac{N_{ppf}}{N_{pix}}\right)^{\frac{t_p}{T}} \propto \frac{\sigma_p}{\sigma_s}$$

Experimental R is normalized to 1 at low rate



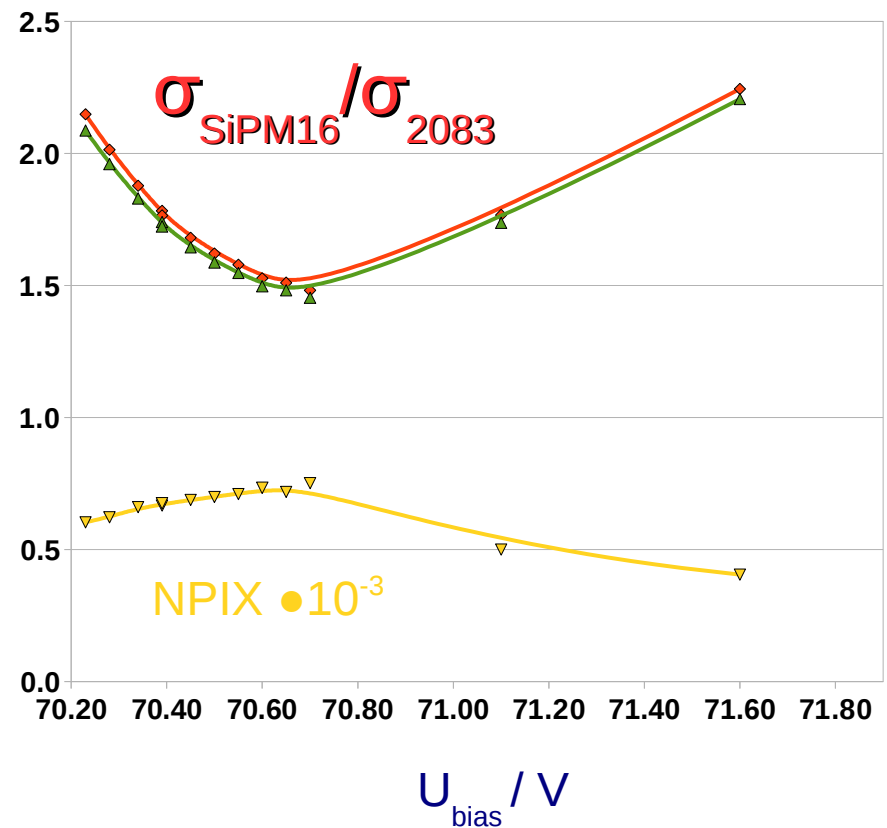
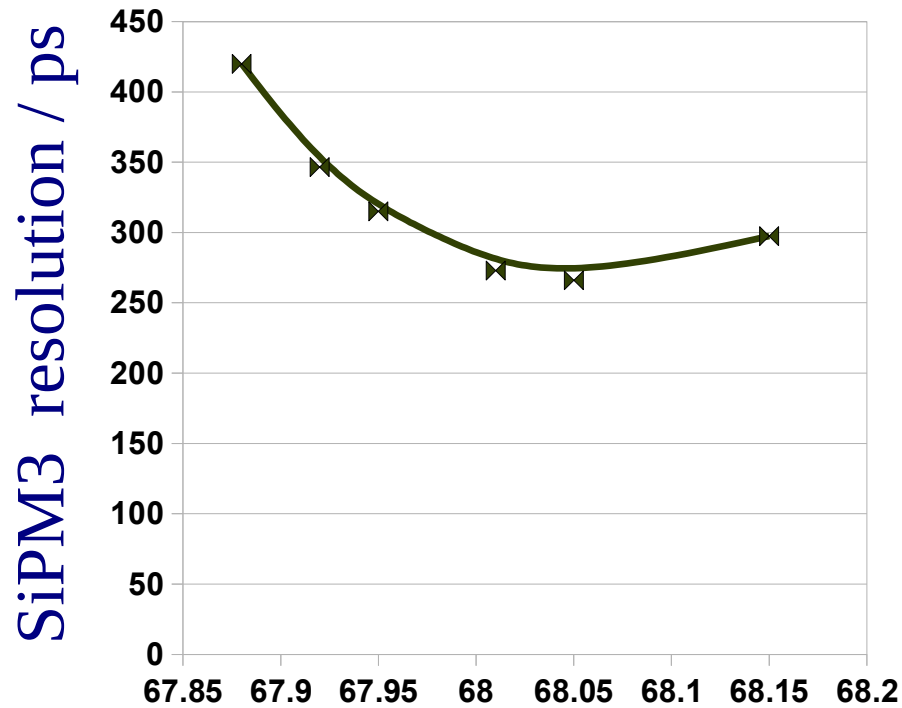
2011/06/10 17.55



2011/06/10 17.59

● “ pixel dead time”

$t_p = 0.8 \pm 0.3$ microsecond.



- The best Time Resolution of SiPM16 at +70.8 V (Nominal +70.39 V)
- Number of fired pixels has a maximum at this bias.
- Pixel dead time will be studied.

Conclusion & Outlook

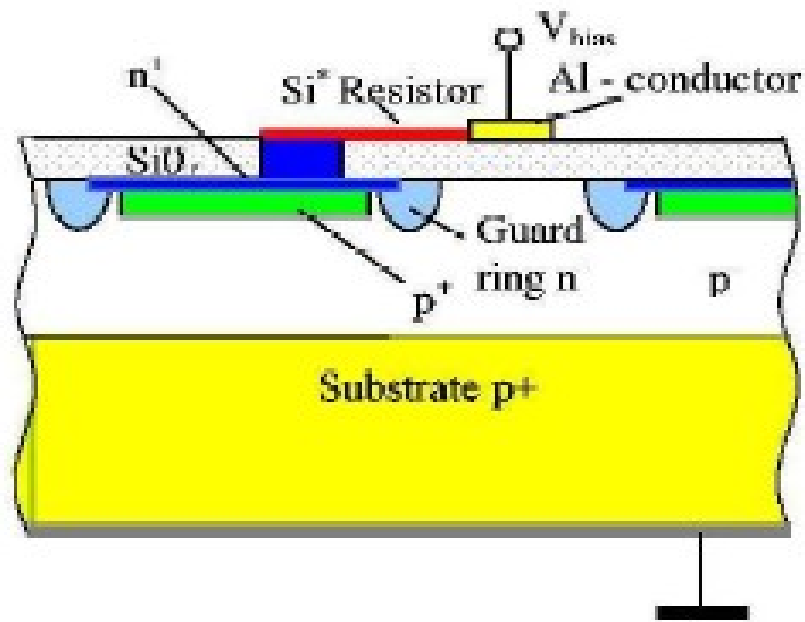
- Resolution of SiPM-1 : ~ 25% better than R2083 (at low rates)
- Resolution of SiPM-3 : ~ same as for R2083
- Resolution of SiPM-16: ~50% worse.
- Quantum efficiency of SiPM: at 475 nm $Q_s = 0.3 \pm 0.05$ (=0.17 for PMT)
- “Pixel dead time” $t_p = (0.8 \pm 0.3) * 10^{-6} \text{s}$.
- Resolution of SiPM3 degrades at $f > 1 \text{MHz}$ due to “pixel dead time” :

$$\sigma_{SiPM3} = (1. \pm 0.05) \sigma_{R2083} \left(\frac{N_{ppf}}{N_{pix}} \right)^{\frac{1}{2}} \left(1 - \exp \left(- \frac{N_{ppf}}{N_{pix}} \right) \right)^{-\frac{1}{2}} \left(1 - \frac{N_{ppf}}{N_{pix}} \right)^{-\frac{t_p f}{2}}$$

Plan

- More accurate measurements with lower reference PMT HV (No saturation effects).
- Measurements with identical SiPMs at both sides of the setup.

$d = 1 \text{ mm}$
 $S = 50 \times 50 \text{ micron}$
 $U_b = 100 \text{ V}$



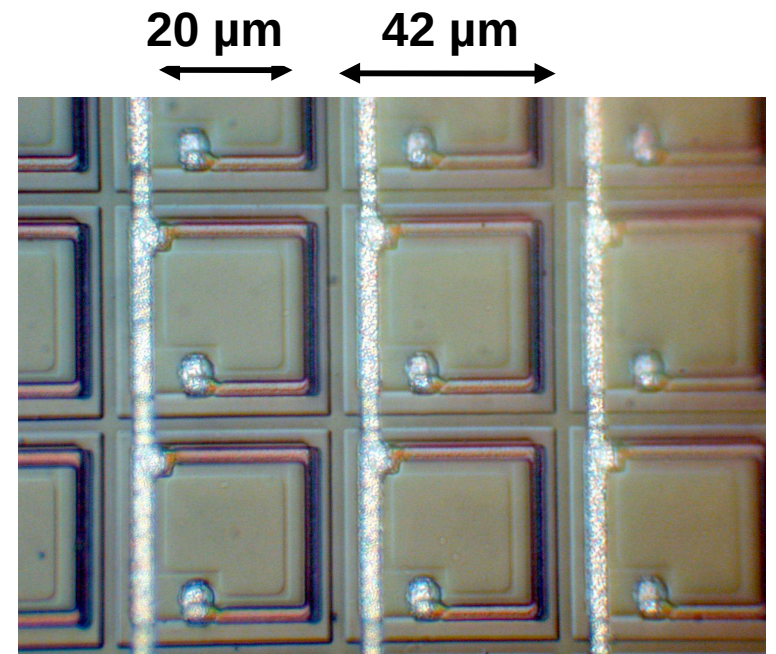
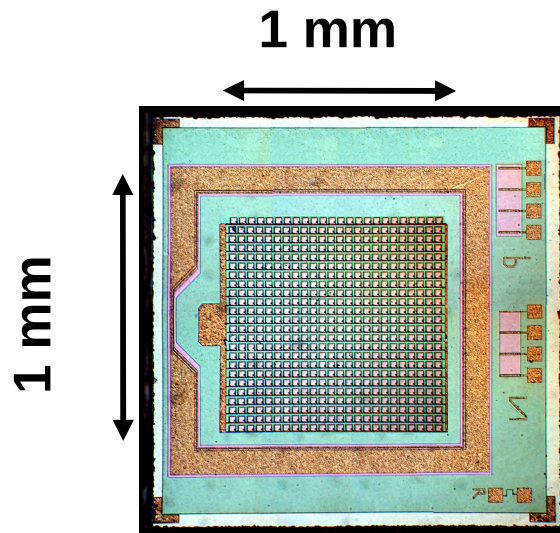
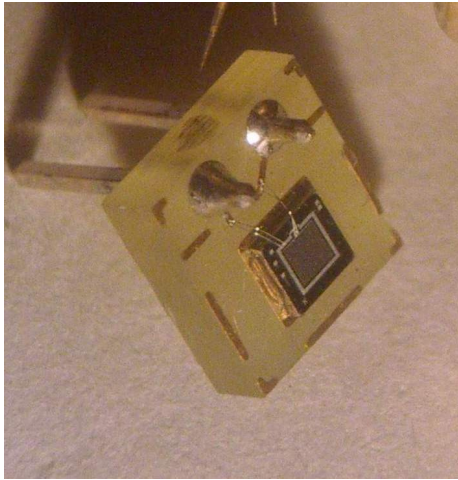
$$Q = CU = \epsilon_0 \epsilon \frac{S}{d} U_b \approx 2 \epsilon \times 10^4 e$$

$$v = \mu E \quad ; \quad 50 < \mu < 500 \left(\frac{\text{cm}^2}{\text{Vs}} \right)$$

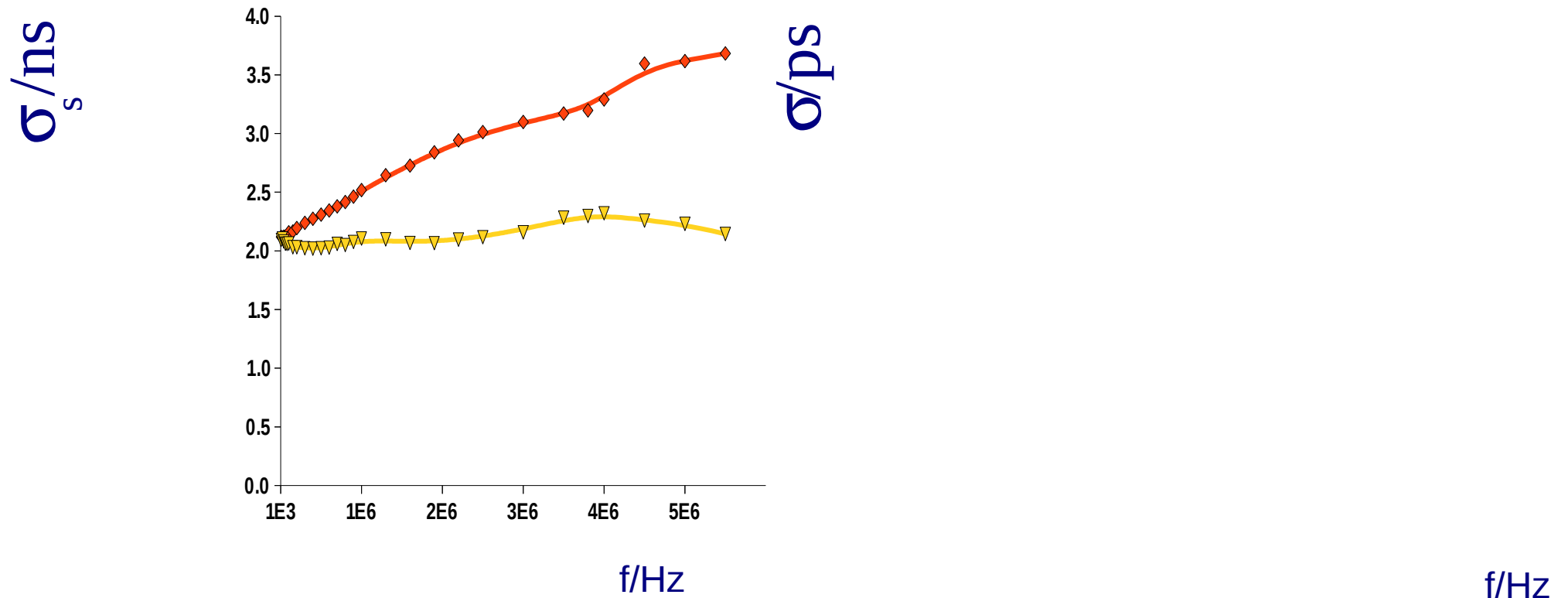
$$\tau_p = \frac{d^2}{\mu U_b} \in (0.2, 2.) (\mu s)$$

- Primary electron may create a p-charge that screens the applied field.
- Hole escape time from the depletion zone may be of 1 microsecond.

First SiPM with 24x24 pixels from MEPhi&PULSAR Enterprise

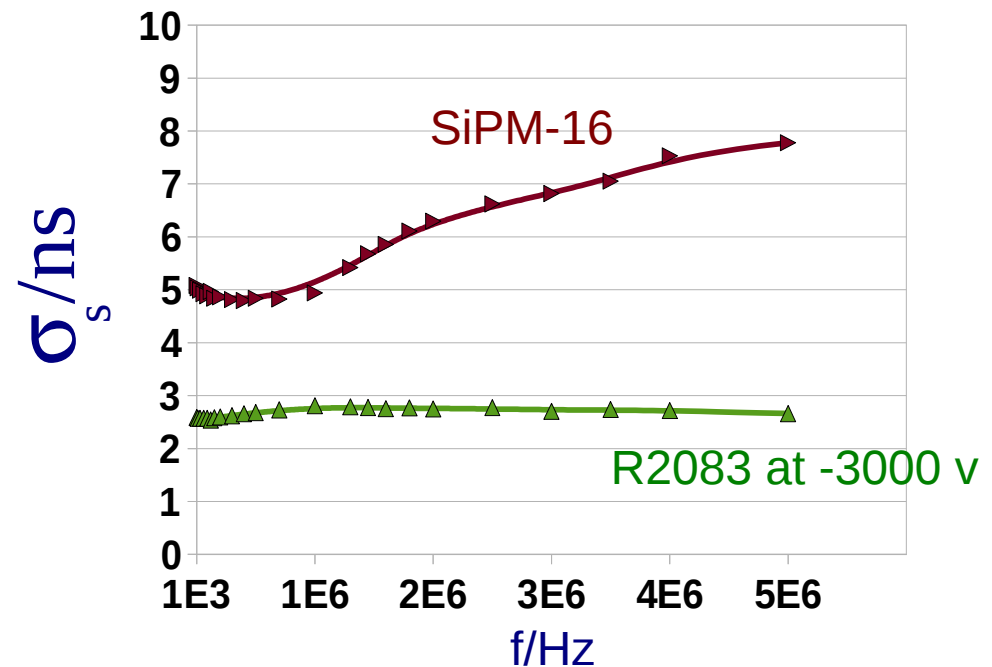
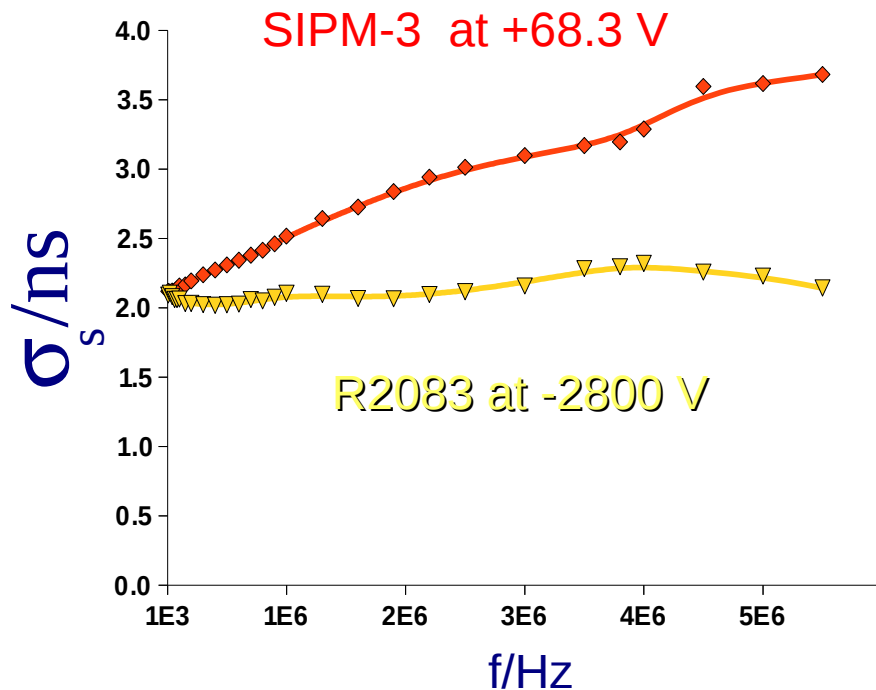


$$\sigma_{SiPM} = \sqrt{\frac{\sigma_s^2}{N} + \sigma_e^2} \quad \text{where } \sigma_e = 23 \text{ ps}$$



$$\sigma_s = 2.0 (ns) + (0.25E-6 ns) f (Hz)$$

SiPM Time Resolution vs. Rate



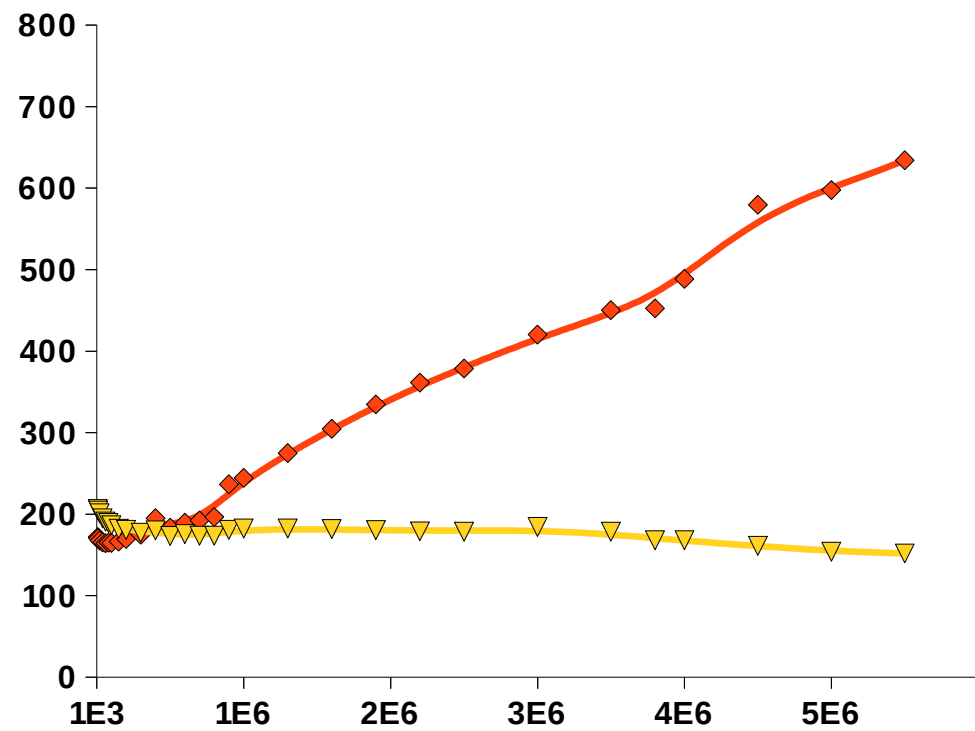
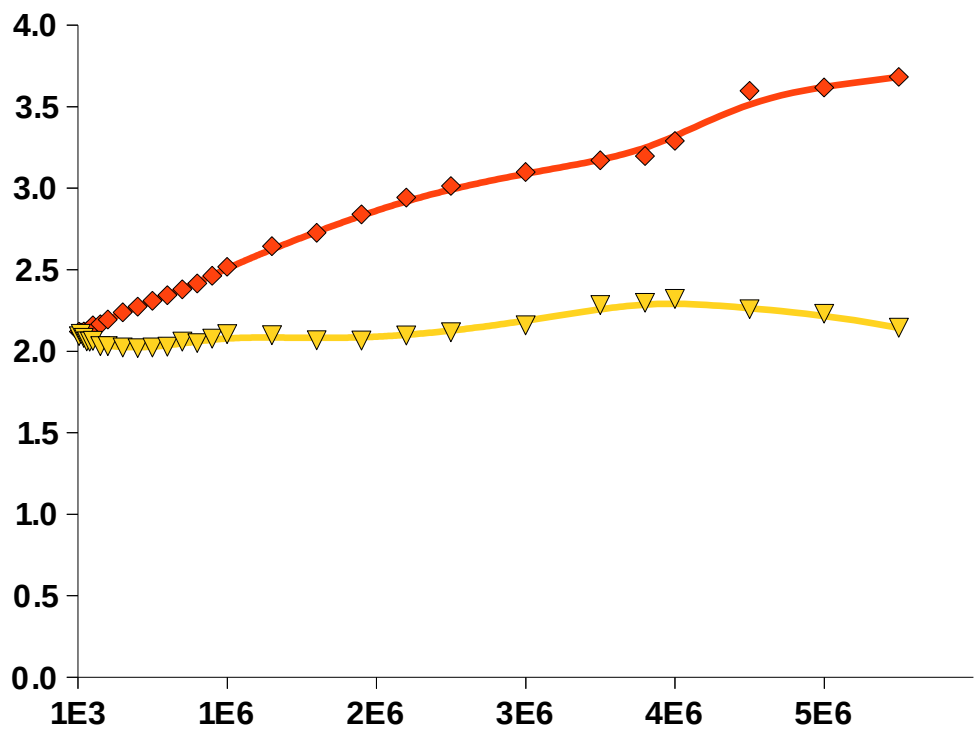
Time Resolution of SiPM may be parametrized as:

$$\sigma_{PM} = \sqrt{\frac{\sigma_s^2}{N} + \sigma_e^2} \quad \text{where } \sigma_e = 23 \text{ ps}$$

Here, σ_s is frequency dependent at high rates:

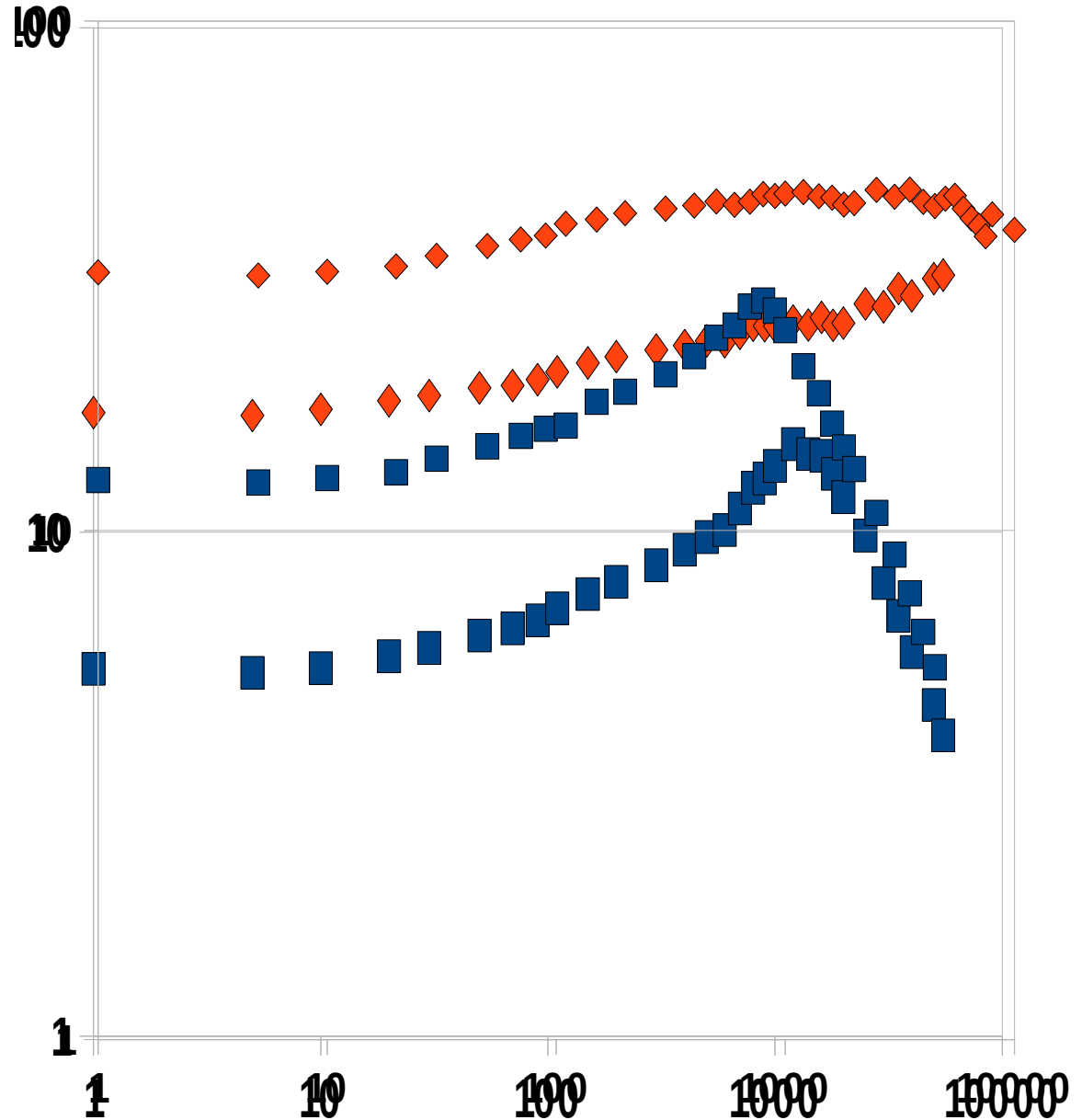
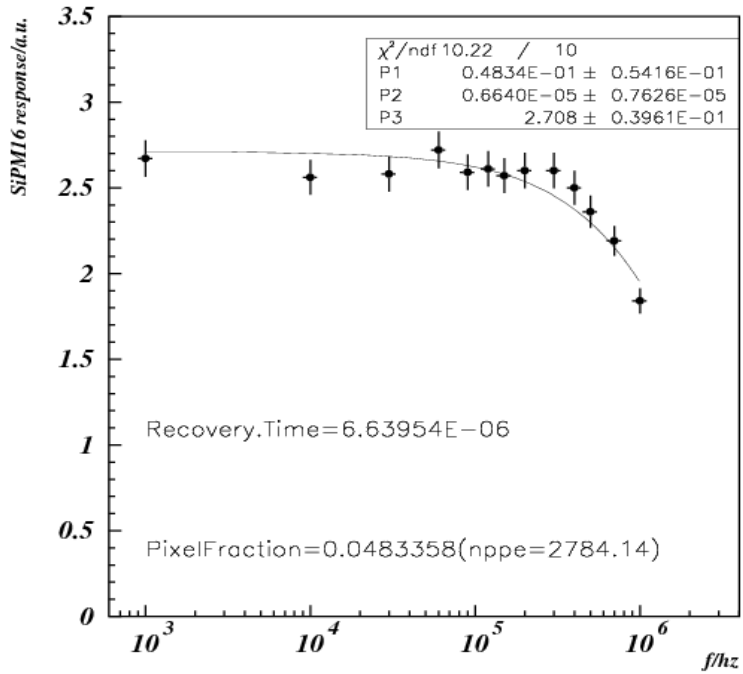
$$\text{SiPM-3: } \sigma_s / \text{ns} = 2.2 + (0.25\text{E-6})f$$

$$\text{SiPM-16: } \sigma_s / \text{ns} = 5.0 + (0.75\text{E-6})f$$

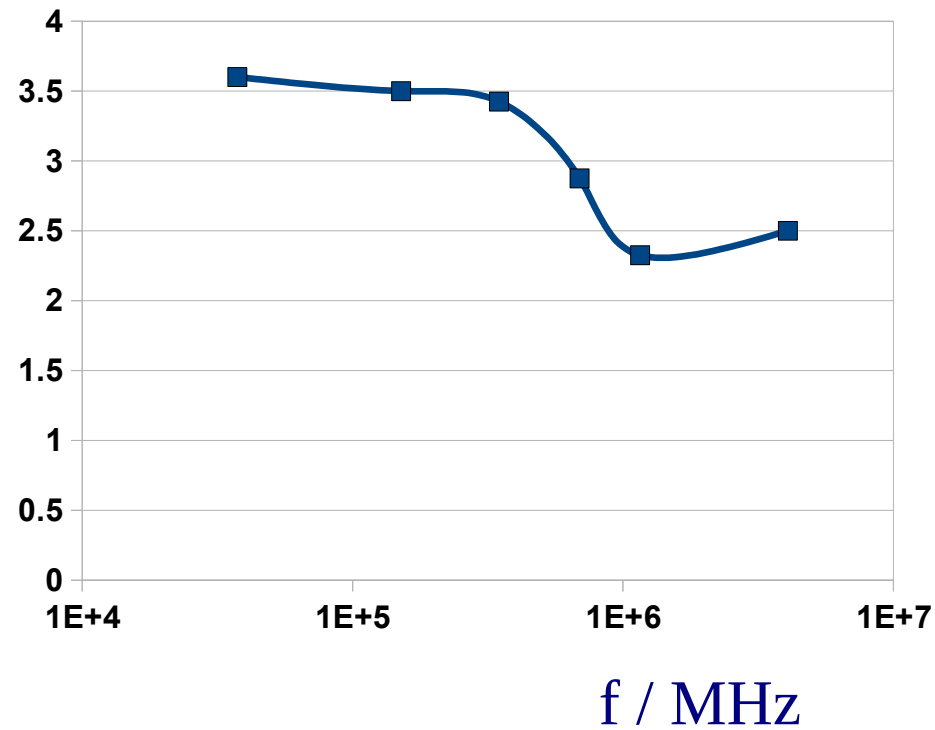


SiPM16 Response vs. Count Rate

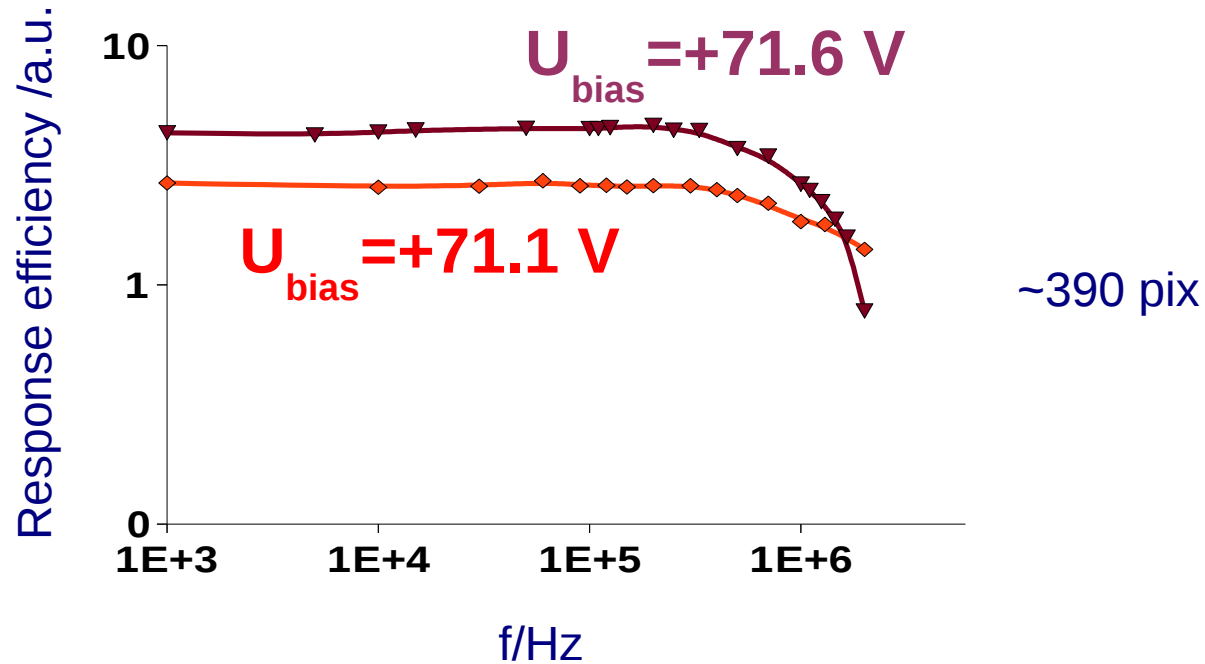
R2083M-2(-3000 V).vs.SiPM3-5(+68.45 V).470nm-LED. Run0815 at 800000 Hz.



Rate effects in SiPM3 signal amplitude



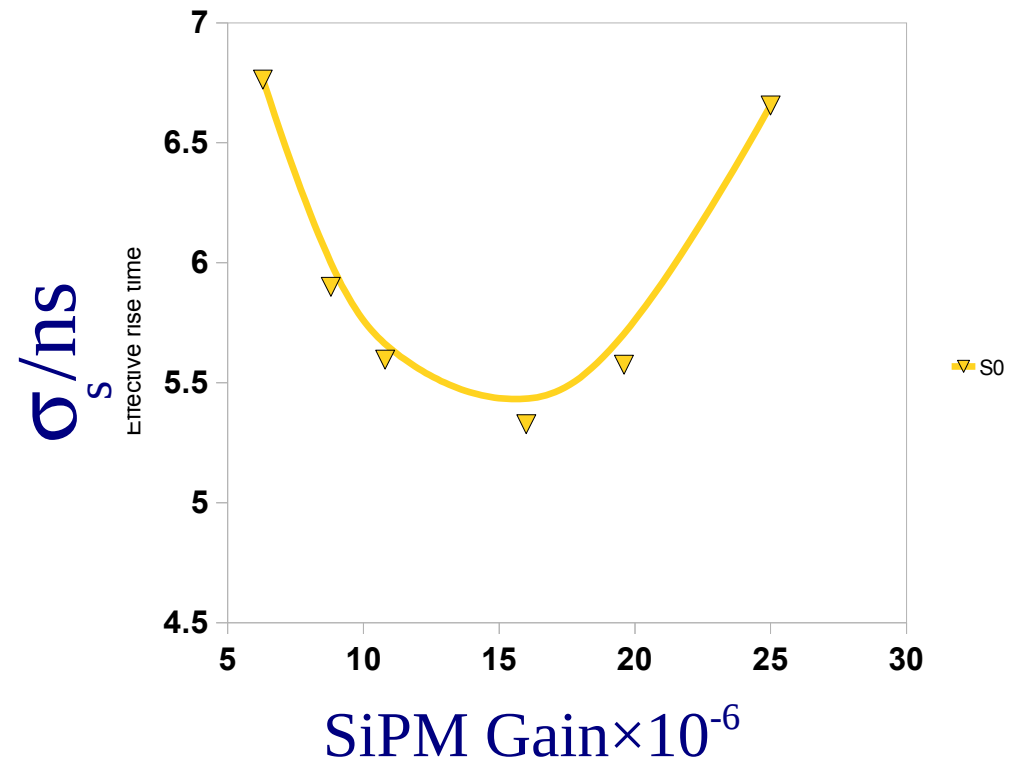
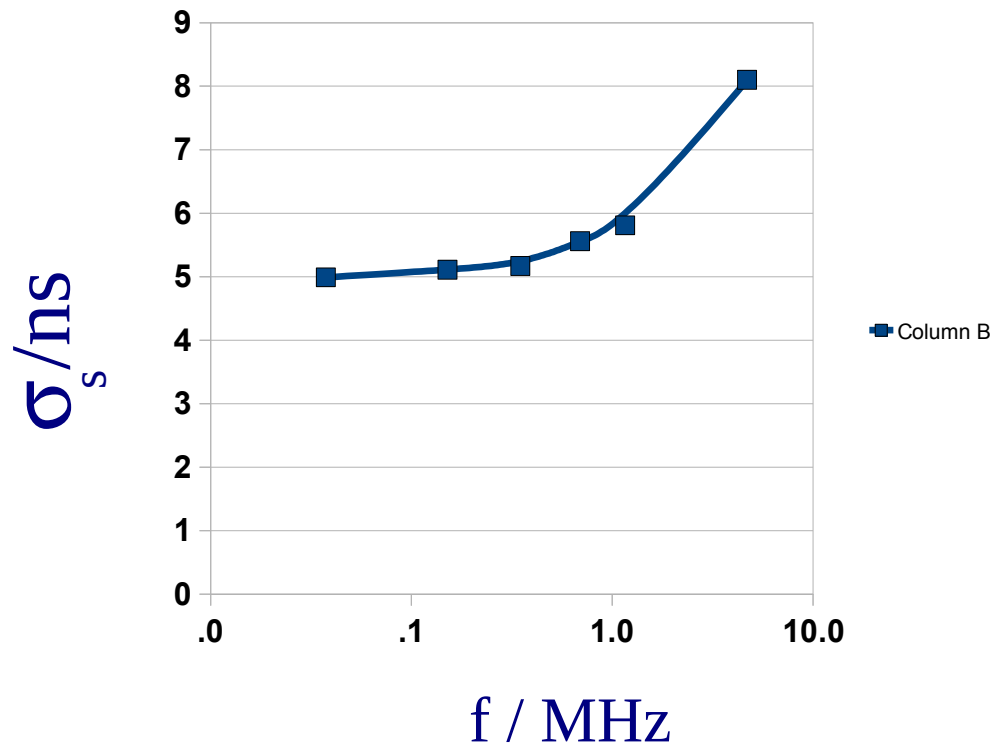
SiPM-16 Response vs. Bias Voltage



- SiPM-16 response drops after 100 KHz, sooner at higher Gain.
- Manifestation of space-charge effect, similar to regular PMT(?)

SiPM Time Resolution vs. Gain and Count Rate

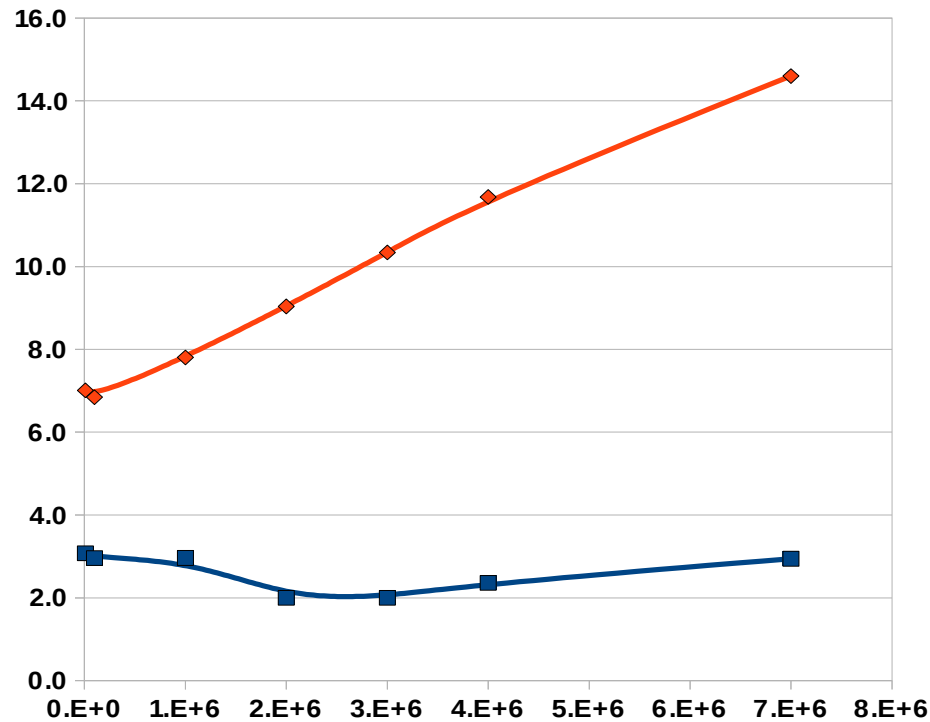
$$\sigma_{SiPM} = \sqrt{\frac{\sigma_s^2}{N} + \sigma_e^2} \quad \text{where } \sigma_e = 23 \text{ ps}$$



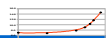
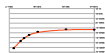
SiPM1 Time Resolution vs. MHz

$$\sigma_{SiPM} = \sqrt{\frac{\sigma_s^2}{N} + \sigma_e^2} \quad \text{where } \sigma_e = 23 \text{ ps}$$

σ_s / ns



$$\sigma_s = 7.0(\text{ns}) + (3.9\text{E-}6 \text{ ns}) f(\text{Hz})$$



SiPM3 Time Resolution vs Gain at 1.2 MHz random rate

$$\sigma_{SiPM} = \sqrt{\frac{\sigma_s^2}{N} + \sigma_e^2} \quad \text{where } \sigma_e = 23 \text{ ps}$$

